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Novel room-temperature ferromagnetism in Gd-doped 2-dimensional  $\text{Ti}_3\text{C}_2\text{T}_x$  MXene semiconductor for spintronics

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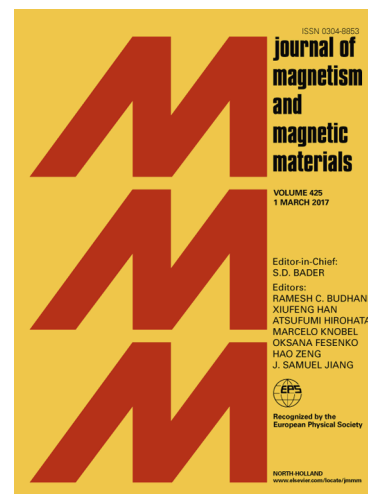
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# Room-temperature ferromagnetism in Gd-doped 2-dimensional $\text{Ti}_3\text{C}_2\text{T}_x$ MXene semiconductor for spintronics

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## ABSTRACT

Two-dimensional nanosheets of MXene ( $\text{Ti}_3\text{C}_2$ ) and  $\text{Gd}^{+3}$ -doped MXene ( $\text{Ti}_3\text{C}_2$ ) have been synthesized superficially by using the cost-effective co-precipitation method. The hexagonal crystal structure doped by Gd was confirmed using X-ray Diffraction. The doping was further confirmed by using scanning electron microscopy, energy dispersive X-ray spectroscopy and Fourier transformed infra-red spectroscopy. Furthermore, UV-Vis spectroscopy absorption spectra, followed by a Tauc-plot, revealed a band-gap value of 1.93eV for Gd-doped MXene, reduced from that for pure MXene (2.06eV). The magnetic measurement of undoped and doped MXene indicate a clear ferromagnetic hysteresis existing at room-temperature. The asymmetric spatial spin-density of states (s-DOS) for undoped MXene is attributed to the existence of spin-up and spin-down electrons of Ti-3d atoms at top and bottom Titanium layers. The strength of one of the spin-type (spin-up) increases more than two-folds at room-temperature after the doping of  $\text{Gd}^{+3}$  cations due to the fact that it contains more unpaired electrons around Fermi level making the MXene more ferromagnetic. The present report establishes the existence of ferromagnetism introduced by doping of  $\text{Gd}^{+3}$  cation in  $\text{Ti}_3\text{C}_2$  MXene at room-temperature making it a suitable candidate for two-dimensional spintronic devices operating at room-temperature.

Keywords: Gadolinium,  $\text{Ti}_3\text{C}_2$ -MXene, Ferromagnetism, Spintronics

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Two-dimensional (2D) ferromagnetic nano-materials have been vigorously pursued for spintronics since the discovery of graphene, as their spin-dependent transport applications are very important for nanoscale data storage memory devices<sup>1 2</sup>. Many researchers focused on 2D ferromagnetic nanoscale materials, mainly the graphene and transition metal dichalcogenides (TMDs). Ferromagnetism is experimentally observed in 2D materials containing graphene with point defects/vacancies<sup>3 4</sup>, stretched graphene nanobubbles<sup>5</sup>, and zig-zag corners at the grain boundaries of TMD nanosheets<sup>6</sup> in which the proposed origin of ferromagnetism is due to unsaturated p-orbitals. However, these 2D systems suffer from severe complications such as poor charge carrier concentration and the deficiency of steady long-range order magnetic interactions at room-temperature since pristine graphene and TMDs are not spin-polarized and are hard to substitutionally dope by transition metals<sup>7</sup>. It has been confirmed in latest studies that nanoscale materials comprising of transition metals (TMs) with open d-orbital shells could reveal a multitude of stimulating properties due to diverse oxidation and spin states, and comparatively greater spin-orbit coupling of the TMs. Therefore, TM-based low-dimensional materials offer an outstanding ground for discovering and developing the internal degrees of freedom of electrons – charge, orbital, and spin – and their relationship for fundamental investigation and device applications<sup>8 9 10 11</sup>. There are various TMs based low-dimensional materials, e.g. dichalcogenides, which may have been potentially exfoliated in experimentation<sup>12 13</sup>. Amongst them, currently, MXenes are actually at the cutting edge of nanotechnology research and have capacity for novel scientific and industrial perspectives<sup>7</sup>.

These MXenes, a newly discovered group that belongs to 2D materials, include transition metal carbides, carbo-nitrides and nitrides. The general formula for MXene is  $M_{n+1}X_nT_x$  (where, M= Sc, Ti, V, Cr, Zr, Nb, Mo, Hf, Ta and X= C, N while n = 1,2,3); the first letter M represents early transition metal, X represents nitrogen or carbon,  $T_x$  shows the surface terminations that can be oxygen (O), hydroxyl (OH) or fluorine (F). The most studied compound among MXenes is  $Ti_3C_2T_x$

. These advanced 2D nanosheets are termed MXenes because they initiate from the MAX phases by eliminating “A” elements and because they are structurally related to graphene<sup>19</sup>. The  $Ti_3C_2T_x$  based MXenes are formed by extracting the aluminium from MAX phase  $Ti_3AlC_2$ <sup>14 15 16 17</sup>. To date, more than 60 MAX phases have been discovered, and many of them have been successfully processed into 2D MXene nanosheets. These MXene layered structures are fundamentally predicted theoretically to be ferromagnetic in nature without any electronic band structure or structural variations and hence, can potentially be fabricated in well crystalline form. Another encouraging point of view regarding spintronics applications of MXenes is their predictable Curie temperature which is predicted to be well above the room-temperature<sup>20</sup>.

Various experimental reports of  $M_{n+1}X_nT_x$  have been presented for different applications such as transparent conductors<sup>21 22</sup>, field effect transistors<sup>23</sup>, supercapacitors<sup>24 25 26</sup>, Li-ion batteries<sup>19 27</sup>, electromagnetic interface shielders<sup>28</sup>, fillers in polymeric composites<sup>29</sup>, hybrid nanocomposites<sup>30</sup>, purifiers<sup>31 32</sup>, dual-responsive surfaces<sup>33</sup>, suitable substrates for dyes<sup>34</sup>, catalysts<sup>35 36</sup>, promising materials for methane storage<sup>37</sup>, and photocatalysts for hydrogen production<sup>38</sup>, as well as being ceramic biomaterials with high photothermal conversion efficiency for cancer therapy<sup>39</sup>. Computationally, many applications have been proposed for MXenes in electronic<sup>40 41 42 43 44</sup>, magnetic<sup>45 46 47 48 49</sup>, optical<sup>50 51</sup>, thermoelectric<sup>48 52 53 54 55 56</sup>, and sensing devices<sup>57</sup>, as well as being new potential materials for catalytic and photocatalytic reactions<sup>18 58 59 60 61 62</sup>, hydrogen storage media<sup>63 64</sup>, and nanoscale superconductivity<sup>65</sup>. Some of the MXenes are predicted to be topological insulators with large band gaps involving only d-orbitals<sup>66 67 68 69</sup>. The  $M_{n+1}X_nT_x$  nanosheets are also expected to be used as ultralow work function materials<sup>70</sup> and Schottky barrier junctions<sup>71 72 73</sup>.

The computational and experimental reports given above have proposed that MXenes are attractive 2D structures due to the subsequent motives: (1) due to their ceramic nature,  $M_{n+1}X_nT_x$  are structurally and chemically stable, (2) these  $M_{n+1}X_nT_x$  can be originated in diverse forms of mono-layer, bi-layer, few-layers and multi-layers, (3)  $M_{n+1}X_nT_x$  can be manufactured as multifaceted

system made up of mixture of light and heavy TMs that makes it promising to adjust the number of outer most electrons and the relativistic spin-orbit interactions. This improves their electronic efficiency and mechanical strength, (4) the thickness of  $M_{n+1}X_nT_x$  mono-layers is well-behaved and controllable which enable us to inspect the quantum confinement associated phenomena, (5) the surfaces of  $M_{n+1}X_nT_x$  can be functionalized with several elemental groups, which suggest opportunities for surface state engineering, (6) comparable to graphene, some of  $M_{n+1}X_nT_x$  reveal massless Dirac dispersions in their band structures adjacent to the Fermi level<sup>66 67 68 69 74</sup>. This opens-up broad possibilities to study and explore the Dirac-based physics<sup>66 67 68 69</sup>. These properties mark  $M_{n+1}X_nT_x$  exceptional candidate among other recognized 2D systems though few of them have not been experimentally perceived yet.

Consequently, for commercial grade devices, large areas with higher carrier concentration 2D room-temperature ferromagnetic nanoscale materials are desirable. The current work is focused on synthesis of undoped and Gadolinium-doped 2D  $Ti_3C_2T_x$  MXene and to study the effect of doping in terms of bandgap, optical properties, and magnetic properties. The present work motivates a new direction for semiconducting 2D materials-based spintronic devices for memory storage applications to be used at room-temperature.

## EXPERIMENTAL

For the selective etching of Aluminium (Al) from MAX (here known as  $Ti_3AlC_2$ ), typically 10 grams of MAX powder was dissolved in 230ml of Hydrofluoric acid (HF, 39 wt%) at room-temperature in closed Teflon bottle under constant magnetic stirring for 66 hours. After the completion of the reaction, the products were washed number of times with ethanol and de-ionized (DI) water in order remove any acidic residues until a pH of 6 was obtained. Followed by vacuum filtration, the powder was dried in a convection oven at 100 °C for about 10 hours. The final product was etched MXene ( $Ti_3C_2$ ) sheets.

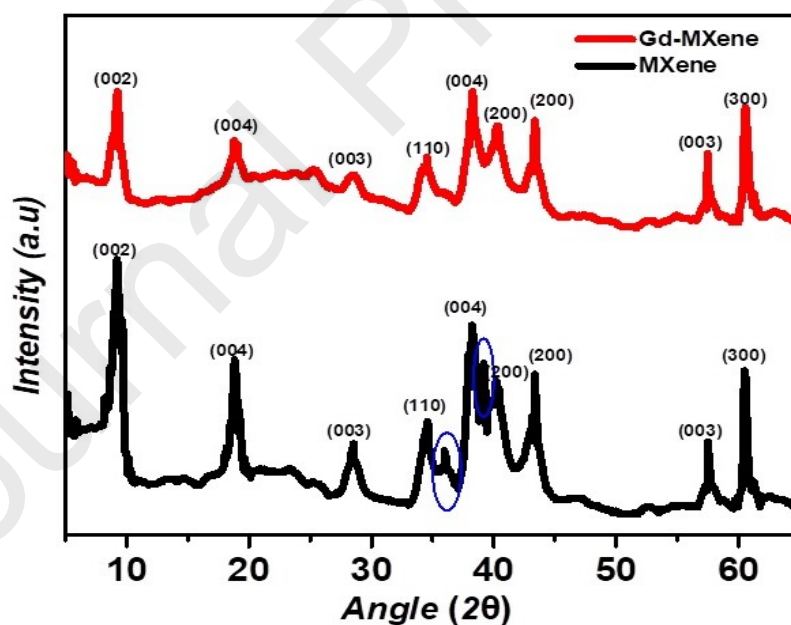
in Supplementary Information (SI), there is simplified reaction occur when  $\text{Ti}_3\text{AlC}_2$  is immersed in HF. We present indication for these reaction with the surface group F and/or OH, which give results in exfoliated layers of MXene ( $\text{Ti}_3\text{C}_2$ ). Hence, it is assumed from reactions SI(2) and SI(3) that terminations are  $-\text{F}$  or  $-\text{OH}$ , in fact they are most possibly combination of both. The layers of  $\text{Ti}_3\text{C}_2$  completely disperse by the Al atoms, which ultimately lead to formation of MAX ( $\text{Ti}_3\text{AlC}_2$ ). After reaction SI(1), Al atoms are detached from  $\text{Ti}_3\text{C}_2$  layers due to which  $\text{Ti}_3\text{C}_2$  layers are also scraped from each other. The main reason to it is the dropping of metallic bonding which is actually the firm holder of the  $\text{Ti}_3\text{C}_2$  layers in presence of Al atoms.<sup>15</sup>

The Gadolinium ( $\text{Gd}^{+3}$ ) doped MXene (General formula:  $\text{Ti}_{3(1-x)}\text{Gd}_x\text{C}_2(\text{OH})_2$ ) with the stoichiometric ratio of 1:1 was synthesized by co-precipitation method.  $\text{Ti}_3\text{C}_2$  solution was prepared in deionized water with a concentration of 0.4mg/ml and was sonicated for 10 minutes at room-temperature. The dopant Gadolinium Nitrate Hexahydrate ( $\text{Gd}(\text{NO}_3)_3 \cdot 6\text{H}_2\text{O}$ ) powder was added to ethylene glycol and acetic acid in a ratio of 1:1, molarity of 0.01 M was used as a solvent and sonicated for 1h at room-temperature. After that, both the separated solutions were mixed together and sonicated for half an hour. After sonication, final solution was put on hot plate for 3h under stirring. The prepared solution was washed with deionized water several times and a homogenous fine powder was obtained, which was put in drying oven at  $100^\circ\text{C}$  for 24 h.

Structural diffraction measurements were performed via X-ray diffractometer (XRD) by using monochromatic Cu-K $\alpha$  radiation wavelength of ( $\lambda=1.5405\text{nm}$ ) under 40 kV voltage source and 200 mA current with  $2\theta$  altering from  $5^\circ$  to  $65^\circ$ . Scanning electron microscopy (SEM) was used to study morphology and particle size of samples. Energy Dispersive Spectrometer (EDS) characterization technique was used to study the chemical ingredients of the samples. The band-gap was calculated by UV-Vis diffused reflectance spectra via UV-Vis spectrophotometer with an integration sphere. Infrared spectra (FTIR) of the samples were measured by using the Fourier-transform (FT-IR) spectrometer. The frequency ranges between  $4000\text{--}400\text{ cm}^{-1}$  using KBr as diluent.

## X-RAY DIFFRACTION

X-ray Diffractometer was used to investigate the crystal structure by powder diffraction patterns of undoped MXene ( $\text{Ti}_3\text{C}_2$ ) and Gd-doped MXene ( $\text{Gd-Ti}_3\text{C}_2$ ) nanosheets as presented in **Figure 1**. All the diffracted peaks of these nanosheets sample are well matched with hexagonal crystal structure as reported earlier<sup>75-76</sup>. The diffraction plane (003) at  $2\theta \sim 28.5^\circ$  represents the characteristics of  $\text{TiO}_2$  peak, in which  $\text{Gd}^{+3}$  shows a complex structure with  $\text{Ti}^{+4}$  on surface in the form of oxides<sup>77</sup>. The peak at  $2\theta \sim 39.2^\circ$  is very sharp in undoped sample which shows the presence of Al in MXene as it usually retained MAX sheet; after doping the peak is suppressed as reported in literature<sup>19</sup>. The peak present at  $34.5^\circ$ ,  $38.1^\circ$ ,  $40.2^\circ$ , shows a small quantity of  $\text{Al}_2\text{O}_3$  as nano-crystals which is not removed completely by etching on the surface of MAX to get MXene<sup>78</sup>.



**Figure 1:** XRD pattern of MXene ( $\text{Ti}_3\text{C}_2$ ) and Gd-doped MXene ( $\text{Gd/Ti}_3\text{C}_2$ ).

The peak at  $2\theta \sim 43^\circ$  and  $2\theta \sim 60.5^\circ$  is suppressed and show the characteristics of titanium carbide in crystal structure<sup>79</sup>. We noticed, overall the intensity of Gd-doped sample has been reduced (i.e.

sharpness suppressed) as compared to undoped MXene. While, there is slight shift in peak positions observed in doped sample as compared to undoped one. This shifting in higher 2 theta values might be caused by two possible effects; ion-exchange mechanism and strong electrostatic interaction, it also gives aspect that there is no intercalation. During the chemical reaction, positive ions are appeared in access and around MXene sheets which create a strong electrostatic potential that interacts with negatively charged surface and cause the formation of a complex interaction between the negative terminations and positive  $Gd^{+3}$  ions. The shifting of peak positions typically caused by this strong electrostatic interaction that makes sure the doping of  $Gd^{+3}$  ion species in the crystal structure of MXene. However, due to larger radius of  $Gd^{+3}$ , the ability to lose electron is greater and probably  $Gd^{+3}$  also creates more positive potential around the surface of MXene. The ionic radii of  $Gd^{+3}$  is (0.938 Å) which is much larger than the ionic radii of  $Ti^{+4}$  (0.605 Å). Thus, it is very hard for  $Gd^{+3}$  ions to substitute into the structure of  $Ti_3C_2$  and replace  $Ti^{+4}$  ions, however, no structure change is supposed for  $Gd^{+3}$  doped samples, indicating that the doped  $Gd^{+3}$  occur at the boundary of crystal rather than into the inner structure of the crystal lattice of  $Ti_3C_2$ <sup>80</sup>.

The lattice parameters of MXene and Gd-doped MXene nanosheets samples are calculated by equation of plane spacing for Hexagonal crystal structure;<sup>81</sup>

$$\frac{1}{d^2} = \frac{4}{3} \left( \frac{h^2 + hk + k^2}{a^2} \right) + \frac{l^2}{c^2}$$

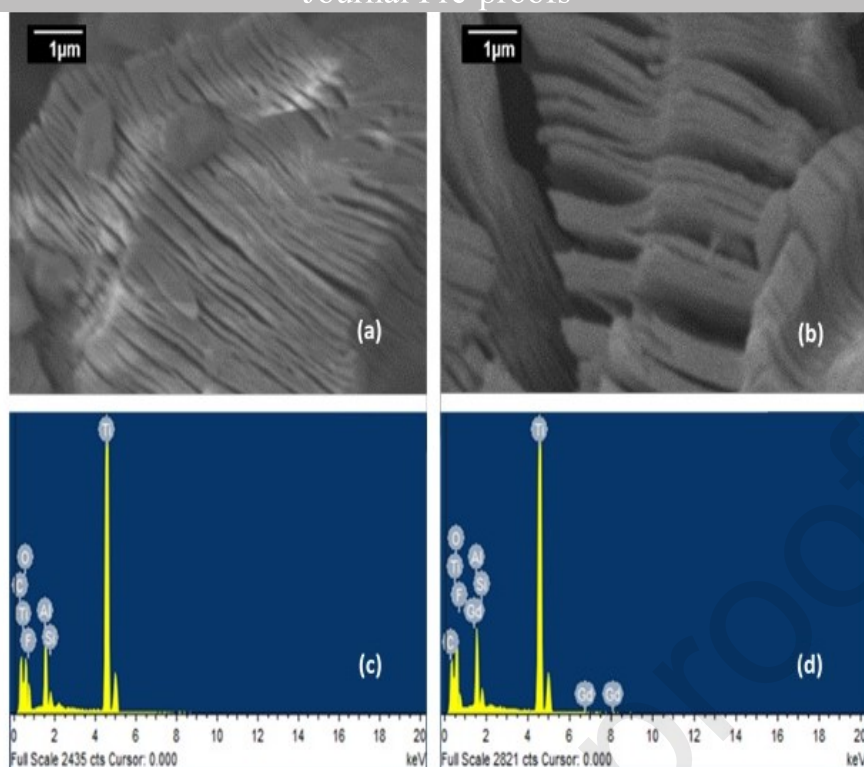
Where, hkl are Miller indices. The lattice parameter  $a=b=5.3\text{Å}$  and  $c=19.20\text{Å}$  for undoped MXene and higher order values  $a=b=5.4\text{Å}$  and  $c=19.30\text{Å}$  for Gd-doped nanosheets has been measured. By using line broadening analysis of X-ray, the particles crystallite size can be calculated<sup>82</sup>. The Scherrer's formula  $D = K\lambda/\beta\cos\theta$  was used to calculate the particle size from broadening the diffraction peak. The particle size for undoped and doped MXene nanosheets are calculated in the range ~19 nm and ~26 nm, respectively.



| X                                       | a (Å) | c (Å)  | c/a   | Crystallite size (nm) |
|---|-------|--------|-------|-----------------------|
| MXene (Ti <sub>3</sub> C <sub>2</sub> ) | 5.3 Å | 19.2 Å | 3.622 | 18.9 nm               |
| Gd-doped Ti <sub>3</sub> C <sub>2</sub> | 5.4 Å | 19.3 Å | 3.574 | 25.6 nm               |

## MORPHOLOGICAL ANALYSIS

Microstructural measurement was performed for Ti<sub>3</sub>C<sub>2</sub>T<sub>x</sub> and Gd-doped Ti<sub>3</sub>C<sub>2</sub>T<sub>x</sub> nanosheets as shown in **Figure 2**. It is observed that the Ti<sub>3</sub>C<sub>2</sub>T<sub>x</sub> has a perfect layered structure, where the nanosheets are clearly separated from each other<sup>76 83</sup> as can be seen in **Figure. 2a**. From SEM image for the doped sample shown in **Figure. 2b**, we did not see any attachment or adsorption of Gd ions with layered structures so we may infer that Gd ions has properly doped into the structure of MXene. The Energy Dispersive X-ray (EDX) spectroscopy provides the information about the elemental compositions in nanosheets samples as presented for undoped and Gd-doped MXene sample in **Figure 2(c, d)**, respectively. The EDS spectra clearly confirmed the presence of elemental peaks of C, F, Si, O, Ti, and Al in both samples with additional signal of Gd in doped MXene sample. The weight (wt. %) concentration of each element has been represented in **table-1**. The presence of Gd-dopant is confirmed as a weight % (0.59) present in the measured spectra. The presence of Al is also confirmed which means that it is not completely removed even after achieving MXene phase.

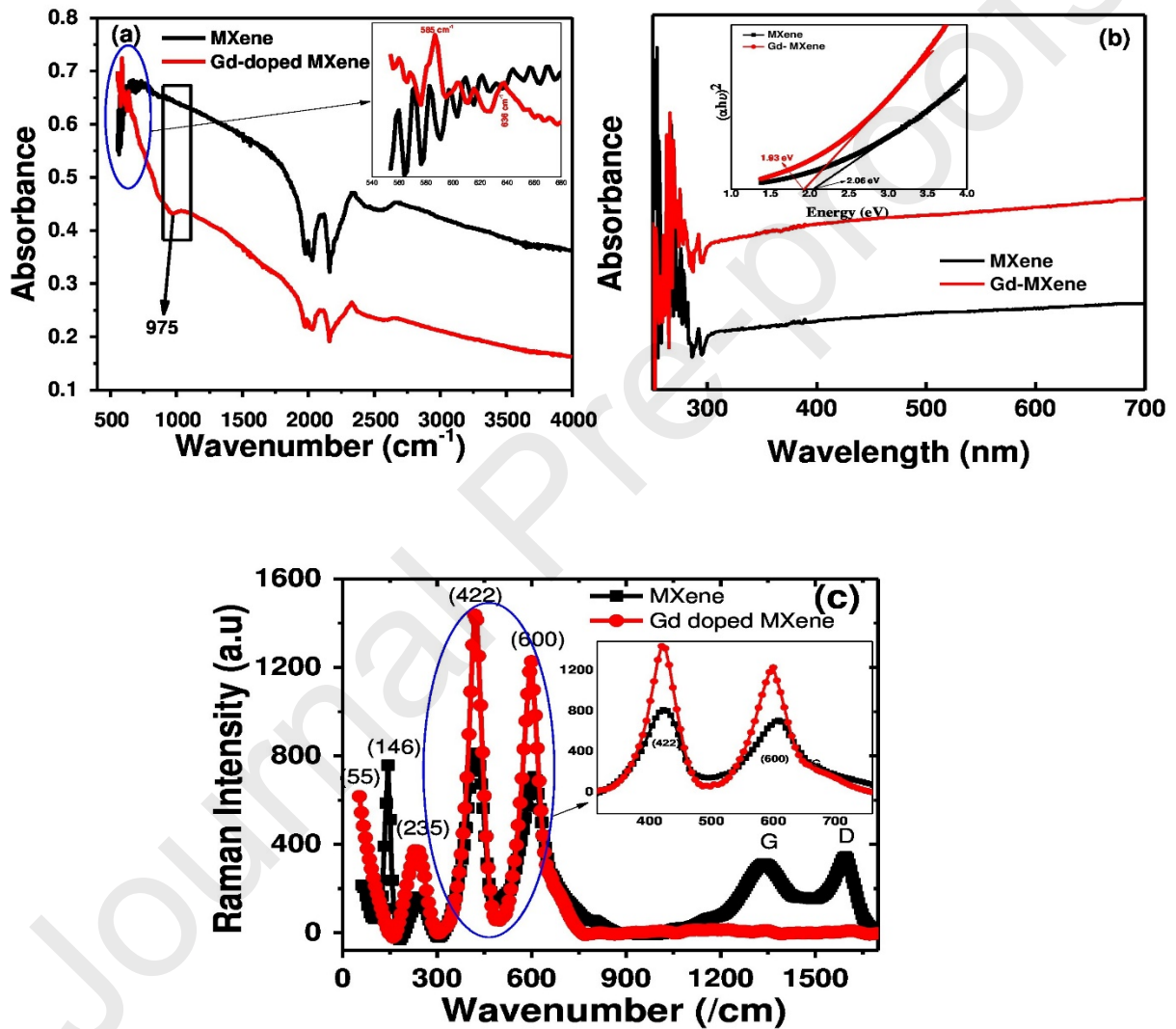


**Figure 2:** (a,b) SEM micrographs of undoped and Gd-doped MXene (c) EDX of undoped MXene (d) EDX of Gd-doped MXene.

## OPTICAL PROPERTIES

Room-temperature FTIR spectra in the range 400-4000  $\text{cm}^{-1}$  for nanosheet samples have been demonstrated in **Figure 3(a)** in determining the extent of oxidation/reduction of materials. A sharp peak at 585  $\text{cm}^{-1}$  and 636  $\text{cm}^{-1}$  is observed (**inset Figure 3(a)**) in spectra of  $\text{Gd}^{+3}$  doped nanosheet sample that shows that  $\text{Gd}^{+3}$  combines with Ti-O on the surface and provides a complex structure in the form of oxide<sup>80</sup>. Interestingly, in FTIR absorption, a small hump at position 975  $\text{cm}^{-1}$  has been observed in Gd-doped samples as compared to pure MXene as represented in **Figure 3(a)**. A small intense peak lies at position 1986  $\text{cm}^{-1}$  may due to stretching of C=O and C=C while at 2094  $\text{cm}^{-1}$ , a sharp high intense peak represents triple bond C≡C stretching absorption. Thus, this stretching is due to the high force constant of the bond<sup>84</sup>. The peak at 2329  $\text{cm}^{-1}$  is usually observed in MXene ( $\text{Ti}_3\text{C}_2$ ) nanosheets<sup>85</sup>.

room-temperature optical absorption spectra of both samples are investigated by using a UV-visible spectrophotometer under the wavelength range (200-700 nm) as is shown in **Figure 3(b)**. The band gap absorption measurement is calculated using the Kubelka-Munk function<sup>86</sup>. The relation between the absorption coefficient ' $\alpha$ ' and the photon energy ' $h\nu$ ' is given in S1. Wherever, ' $A$ ' is ineffective equation constant, ' $h$ ' is Plank's constant, ' $\nu$ ' is light frequency, ' $E_g$ ' represents band gap energy, respectively<sup>87</sup>.



**Figure 3:** (a) FTIR (b) UV-Vis absorption spectra; (inset) bandgap energy (c) Room-temperature Raman spectra.

The value of “n” is for the possible absorbance ways to determine the type of transition, n=1 for direct band gap transition and n=4 for the indirect bandgap transition. The band gap of undoped and

Gd-doped MXene sample was obtained by plotting  $(\alpha h\nu)^2$  against band gap energy  $E_g$

also known as Tauc's plot method<sup>91-92</sup> such as presented in inset of **Figure 3(b)**. The band gap of MXene is established to be 2.06 eV and the band gap for the Gd-doped MXene is reduced to 1.93 eV. For Gd-doped MXene nanosheets, the red shift is observed in the absorption spectra as compared to pure MXene. In Gd-doped MXene, the slight reduction in the band gap energy has been observed as reported previously<sup>93</sup>. As  $E_g$  for Gd-doped MXene is smaller than those for un-doped MXene, it is an indication that new electronic levels (sub-bands) will be introduced by doping ions inside the MXene band-gap as reported earlier for 2-dimensional nanosheets semiconductor systems

86 91 94 95 96

Raman spectrum of  $Ti_3C_2$  MXenes has several broad peaks ranging from 50 to 1600  $cm^{-1}$ , which can be assigned to non-stoichiometric titanium carbide as shown in **Figure 3(c)**. According to the crystallographic structure of  $Ti_3C_2$ , the 5 atoms of the primitive unit cell in the  $Ti_3C_2$  nanosheet contribute rise to 12 optical modes and 3 acoustic modes at the  $\Gamma$  point of the Brillouin zone<sup>97</sup>. The optical phonons at the center of the Brillouin zone for  $Ti_3C_2$  are given in SI<sup>97-99</sup>. All Raman vibration modes of Gd-doped sample are shifted toward lower wavenumber as compared to undoped sample as shown inset Figure 3(c). While interestingly, we noticed that the intensity of each mode has enhanced in Gd-doped as compared to undoped sample.

In literature for  $Ti_3AlC_2$ , phonon vibration at 150  $cm^{-1}$  was assigned to the Al atoms related vibration modes<sup>100</sup>. The Raman peak lies at 146  $cm^{-1}$  may be due to phonon vibration of  $Ti_3AlC_2$  (MAX) as reported previously<sup>101</sup>. In literature, frequency associated with doubly degenerated  $E_g$  modes at 146  $cm^{-1}$  in the bare  $Ti_3C_2$  nanosheet may reflect the main contribution is from in-plane vibrations of  $Ti_2$  and C atoms which may correspond to the anatase crystal structure<sup>23</sup>. In Gd-doped sample, we did not observe mode at 146  $cm^{-1}$ , usually lower-frequency (<500  $cm^{-1}$ ) phonons are due to collaborative motion of all atoms in the nanosheets. It is noteworthy that no robust signal of  $TiO_2$  was detected<sup>102</sup> (as we obtained 146  $cm^{-1}$  in pure sample) in Gd-doped MXene sample, indicating that either the  $Ti_3C_2T_x$  sheets are not oxidized, or limited MXene flakes are oxidized that is beyond the detection of Raman technique, indicating low density of anatase  $TiO_2$  on the surface of  $Ti_3C_2T_x$ .

The remaining peaks of the pristine  $\text{Ti}_3\text{C}_2$  nanosheet sample and Gd-doped MXene belong to Ti–C vibrations. In the  $\text{Ti}_3\text{C}_2$  nanosheets, the modes assigned at  $235\text{ cm}^{-1}$  and  $600\text{ cm}^{-1}$  position relates with  $A_{1g}$  group and correspond to out-of-plane stretching vibrations of  $\text{Ti}_2$  and C, respectively<sup>97-99</sup>. The vibrational phonon at position  $422\text{ cm}^{-1}$  belongs to  $E_g$  Raman modes that may be assigned to  $\text{Ti}_3\text{C}_2(\text{OH})_2$  phase existence for in-plane modes vibrations<sup>99</sup>. The two broad peaks between  $1350\text{ cm}^{-1}$  and  $1580\text{ cm}^{-1}$  belong to the D-band (is associated with disordered graphite structure and defects) and G-band (originates from the signal from graphite) of graphitic carbon<sup>103</sup>. Both G and D peaks are due to  $\text{sp}^2$  sites. The G-mode peak is associated with the stretching of the C-C bond in carbon materials and is common to all  $\text{sp}^2$  carbon systems in both, rings and chains<sup>104</sup>. The D mode peak depends on  $\text{sp}^2$  fraction and order and appears only if the  $\text{sp}^2$  is in disordered rings. In undoped MXene sample, the presence of carbon sheets (G and D band) covered by  $\text{TiO}_2$  (mode  $146\text{ cm}^{-1}$ ) particles on the surface implies that the innermost Ti atoms in the MXene structure migrated outward to react with oxygen. This outward migration of Ti is similar to what has been observed previously during the oxidation of TiN<sup>105</sup>. A different interesting observation in Raman spectra is the absence of D and G bands after Gd-doping in  $\text{Ti}_3\text{C}_2\text{T}_x$  nanosheets that might indicate the deformation of carbon<sup>106</sup>.

## MAGNETIC ANALYSIS

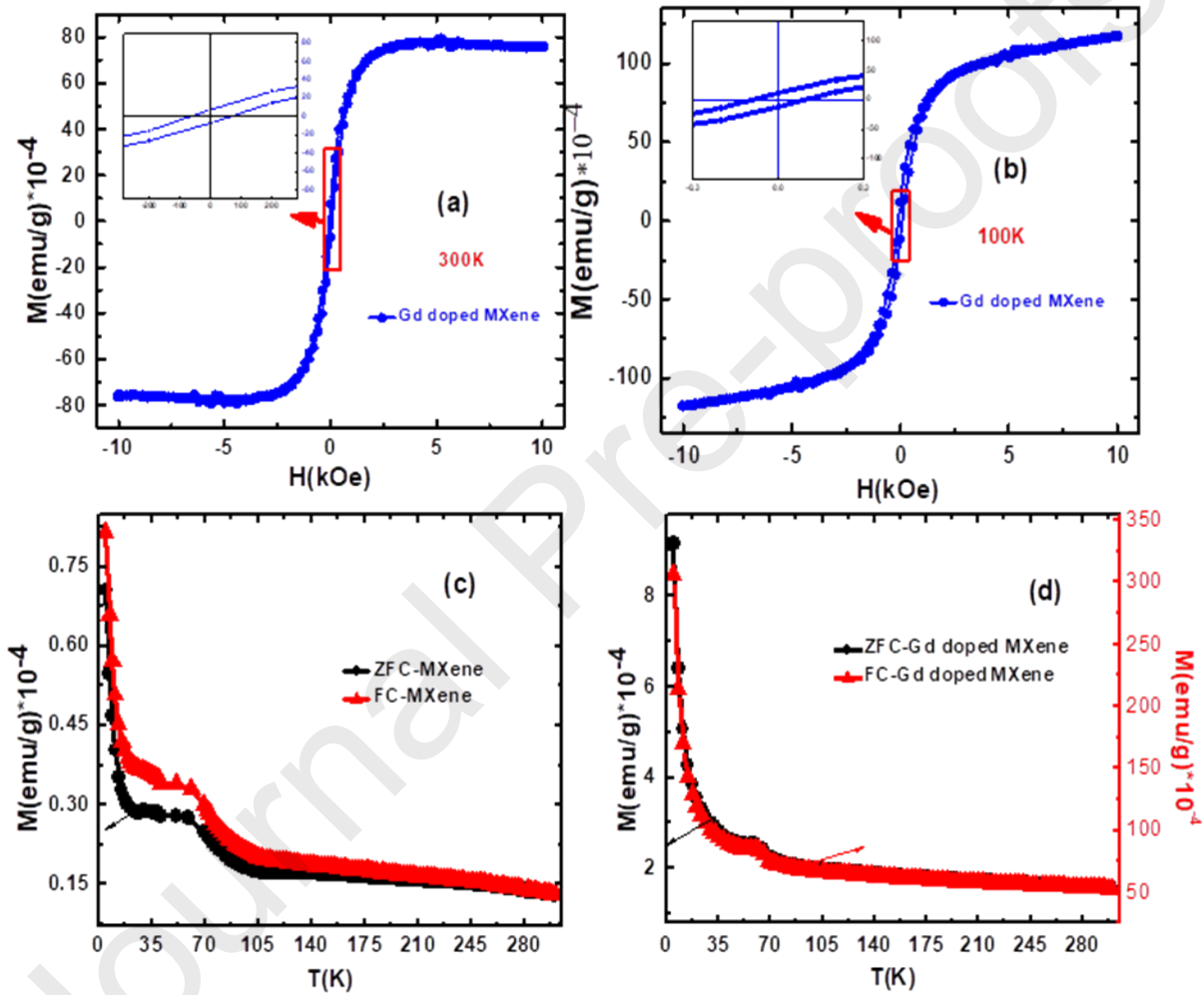
The magnetic hysteresis loops for Gd-doped MXene measured at 300K and 100K are shown in **Figure 4(a, b)**. Also, to remove the background signal of the machine that may create its own stray magnetic field that may induce anisotropic magnetic effect, the system was calibrated by using an oscillatory field in order to eliminate the entire stray fields among the coils, so the real magnetic behavior of the sample could be observed. After we were sure of the neutral stray magnetic field, we performed the measurement. The “S-shaped” curve at room temperature with saturation magnetization (Ms)  $22 \times 10^{-4} \text{ emu/g}$  for undoped MXene (**Fig. S1**) and  $80 \times 10^{-4} \text{ emu/g}$  for Gd-doped MXene nanosheets at magnetic field of 10 kOe are seen for both samples. At room-temperature, we

noticed the fluctuation in data points of undoped MXene sample as compared to very smooth data points of Gd-doped nanosheets which indicates that undoped sample may require more magnetic fields to stabilize at 300K relative to Gd-doped sample. The measured values of coercivity in kOe ( $H_c = 0.0887$ ) and remnant magnetization ( $M_r = 0.2298 \times 10^{-4} \text{ emu/g}$ ) for doped MXene were measured. At the temperature of 100K, the non-saturated hysteresis curve of the undoped and doped samples are shown in **Figures SI and 4(b)**, respectively. It can be seen that the saturation magnetization for undoped and doped samples are  $3.529 \times 10^{-4} \text{ emu/g}$  and  $120 \times 10^{-4} \text{ emu/g}$ , respectively. These samples showed weak ferromagnetism as demonstrated in Figure SI and Figure 4. The slope of curves at 100K increased as compared to 300K measurements, however another anomaly is found that the  $M_s$  value at 100K has been decreased by 5 times for undoped sample as equated to 300K. While, usual behavior has been observed for Gd-doped MXene sample,  $M_s$  value increased by factor of almost 42 as measurement temperature decreased from 300K to 100K. This net spin moment interacts more as thermal fluctuation reduces and wave function of unpaired electrons overlaps more vigorously, ultimately saturation magnetization enhances. The increase in saturation magnetization, decrease in coercive fields and increase in remnant magnetization for Gd-doped MXene as compared to undoped MXene might be attributed to the ferromagnetic nature of  $\text{Gd}^{+3}$  cation which possess excess unpaired spins of electrons and thus, have more net magnetic moment. As a result, the doped MXene shows a good ferromagnetic behavior at room-temperature<sup>107</sup>

108 109 110 111 112 113

It is to be noted that the net magnetic moment for ZFC is lower than for FC due to fact that the magnetic field for FC curves overcome the anisotropic effect of magnetic domains. However, this may also be attributed to the presence of functional groups such as  $-\text{OH}$  or  $-\text{O}-\text{I}$ s which may create an attraction for electron cloud due to its more electronegativity than the Ti and C -cations<sup>48</sup>. It was reported by S. Zhao et al. that the spatial spin-density of states (s-DOS) for spin-up electrons exist at upper layer of Ti-3d cation whereas the s-DOS for spin-down electrons lie at the bottom Ti-3d electrons resulting in an asymmetric net spin moment within the  $\text{Ti}_3\text{C}_2$  MXene layers<sup>16</sup>. This explains

the presence of low net magnetic moment in undoped MXene. However, it was observed that the doping of Gadolinium cation results in strong magnetic hysteresis loop and large net magnetic moment which indicates that the resultant spatial spin-density of states exceeds more for one type of spin, i.e. spin-up than the other spin. This results in increased magnetic moment for the Gd-doped MXene than for the undoped MXene even for a very small doping concentration.



**Figure 4:** (a) and (b) M-H curves for Gd-doped MXene at 300K and 100K, respectively, (c) and (d) field cool (FC) and zero field cool (ZFC) curves measured at 1000 Oe for undoped MXene and Gd-doped MXene, respectively.

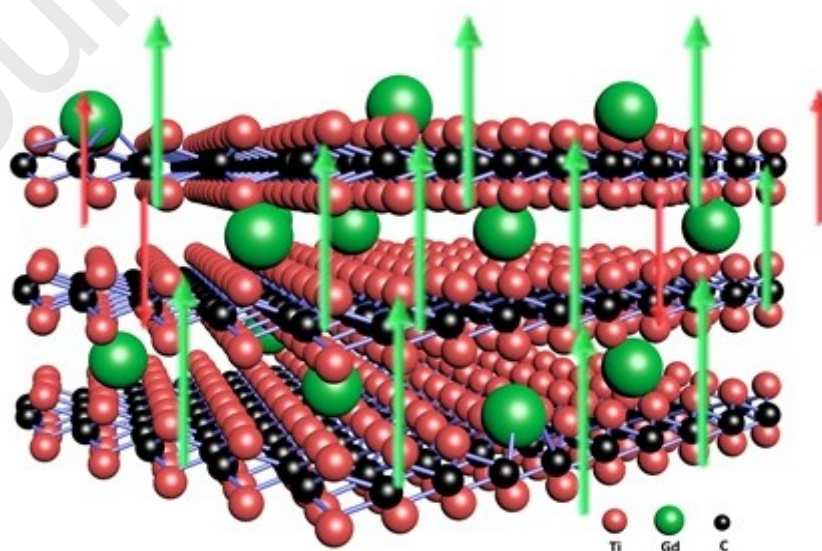
The zero-field cooled (ZFC) and field cooled (FC) temperature measurements known as  $M(T)$  of these nanosheets samples were measured at magnetic field strength of 1000 Oe as presented in



Figure 4(c, d) for undoped and Gd-doped samples, respectively. These FC and ZFC curves show the ferro- to para- magnetic phase transition as temperature increased from 5K to 300K. For both samples, the values of FC and ZFC remains well above zero, which is a clear indication of the interaction among unpaired electrons exist and net magnetization will be attained even at room-temperature. From these curves, we noticed that almost FC and ZFC values remains same for undoped MXene while FC values of Gd-doped nanosheets are much higher (e.g. maximum value is  $340 \times 10^{-4} \text{emu/g}$ ) than ZFC values (e.g. maximum value is  $8.2 \times 10^{-4} \text{emu/g}$ ). We found one discrepancy during  $M(T)$  measurements for both samples. We noticed decreasing trend of magnetic moment with increasing temperatures during FC/ZFC measurements however an irregular behavior detected in Figure 4(c, d) for both samples which shows splitting of the FC/ZFC curves at low temperatures. This irregular behavior might be due to the presence of extra impurities (i.e. impurities are present as discussed in the XRD section as  $\text{TiC}$  and  $\text{TiO}_2$ ). Usually, these impurities are unavoidable due to the nature of chemical synthesis route followed as well as the etching process to get MXene itself from the parent MAX phases.

These observations may suggest that the undoped MXene need more field strength as compared to Gd-doped nanosheets to well align its all unpaired domain in the direction of applied field. The  $M(T)$  curves also indicate there is an increase in magnitude and stability of Gd-doped MXene compared to the undoped MXene which makes it a suitable candidate for spintronics applications based on two-dimensional materials.

**Figure 5** summarizes the overall synthesis and reasoning for origin of ferromagnetism in Gd-doped MXene at room-temperature.





## CONCLUSION

The 2D undoped and Gd-doped  $\text{Ti}_3\text{C}_2$ -MXene sheets were prepared using co-precipitation method. The structural, morphological, elemental and bandgap characterizations showed the successful doping of Gadolinium into the MXene sheets. The Gd-doped MXene indicate its semi-conductive nature. The magnetic measurement showed that the Gd-doped sample possess a high magnetic moment at room-temperature with a stable ferromagnetic hysteresis loop. The origin of magnetism lies in the fact that the electrons in Ti-3d has measurable spin-density of states around Fermi level which enhances upon doping of ferromagnetic Gadolinium cation, making it a perfect soft ferromagnet. The successful doping, reduction of the band-gap and introduction of strong ferromagnetic signal at room-temperature makes our sample a suitable candidate for spintronic devices and opens up more scope for the rare-earth elements doping into MXene sheets.

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#### Highlights:

1. This is the first report on rare-earth Gadolinium cation ( $Gd^{+3}$ ) doping in two-dimensional  $Ti_3C_2$ -MXene.
2. The bandgap of the MXene decreased from 2.06eV to 1.93eV after the successful doping of Gd cation. The undoped  $Ti_3C_2$ -MXene showed weak signature of ferromagnetism at low-temperature and room-temperature however, the magnetic moment was low and not stable at room-temperature.
3. This experimental evidence gives evidence of ferromagnetism in 2D MXene suitable for 2D spintronics.